

ESAC33M(C,N,D) (8A)

(200V / 8A)

FAST RECOVERY DIODE

Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

Applications

- High speed switching

Maximum ratings and characteristics

- Absolute maximum ratings

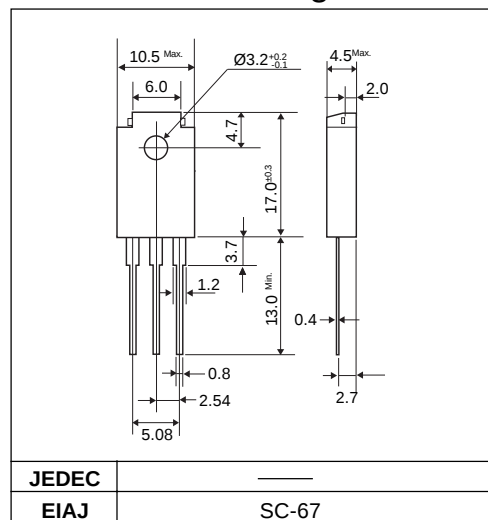
Item	Symbol	Conditions	Rating	Unit
			-02	
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		200	V
Average output current	I_o	Square wave, duty=1/2, $T_c=95^{\circ}\text{C}$	8*	A
Surge current	I_{FSM}	Sine wave 10ms	30	A
Operating junction temperature	T_j		-40 to +150	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-40 to +150	$^{\circ}\text{C}$

*Average forward current of centertap full wave connection

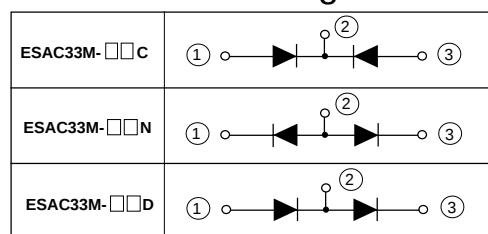
- Electrical characteristics ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=2.0\text{A}$	1.4	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	500	μA
Reverse recovery time	t_{rr}	$I_F=0.1\text{A}$, $I_R=0.1\text{A}$	100	ns
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5	$^{\circ}\text{C/W}$

Outline drawings, mm

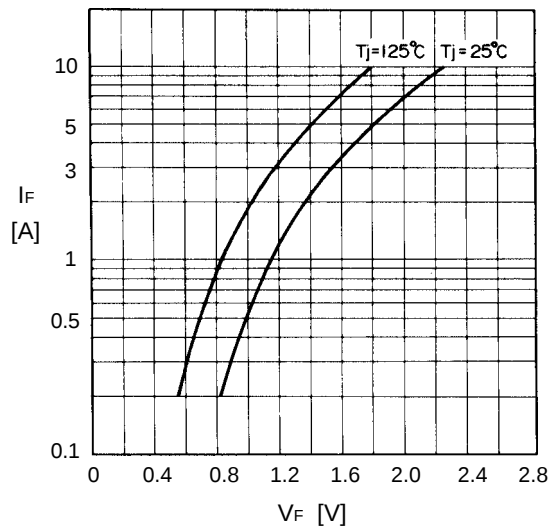


Connection diagram

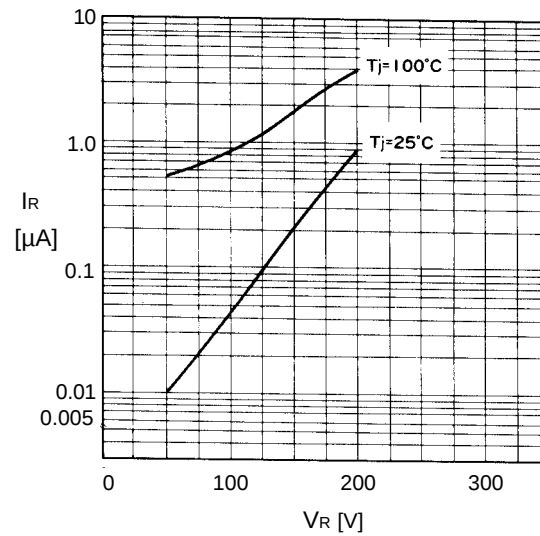


Characteristics

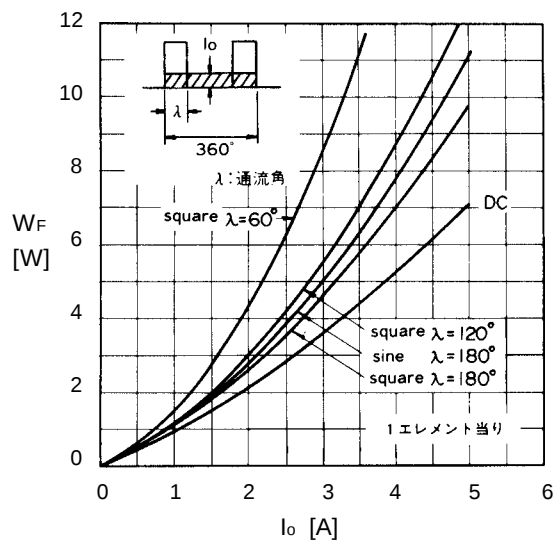
Forward characteristics



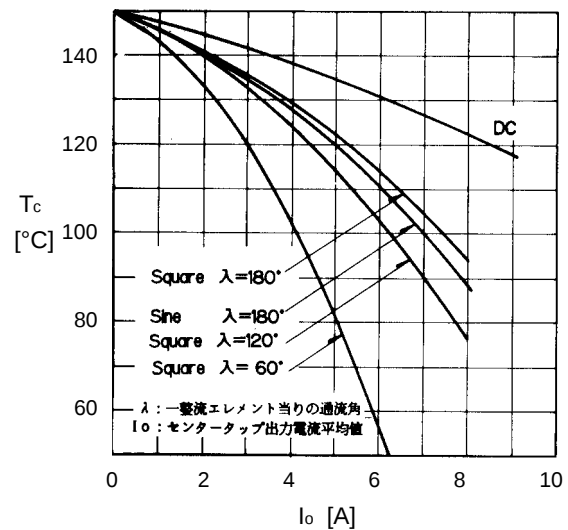
Reverse characteristics



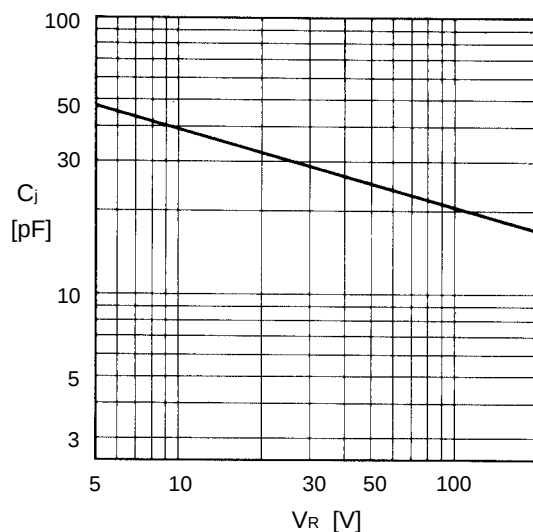
Forward power dissipation



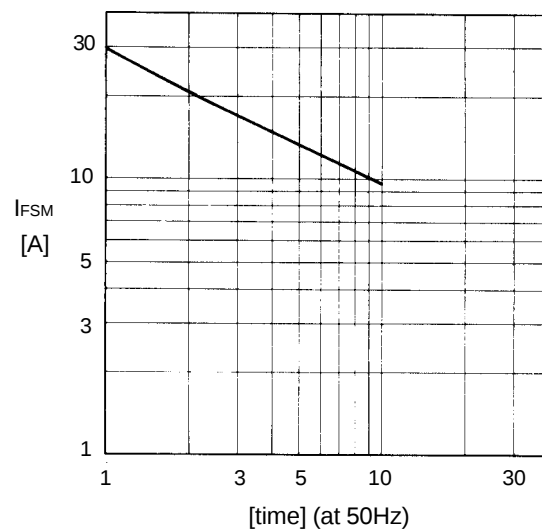
Output current-case temperature



Junction capacitance characteristics



Surge capability



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